

T808 750-20-26

Key Parameters

V_{DRM}	2000~2600	V
$I_{T(AV)}$	750	A
I_{TSM}	11.0	kA
V_{TO}	0.95	V
r_T	0.5	mΩ

Applications

- Traction drive
- Motor drive
- Industry converter

Features

- Double-side cooling
- High power capability
- Low loss

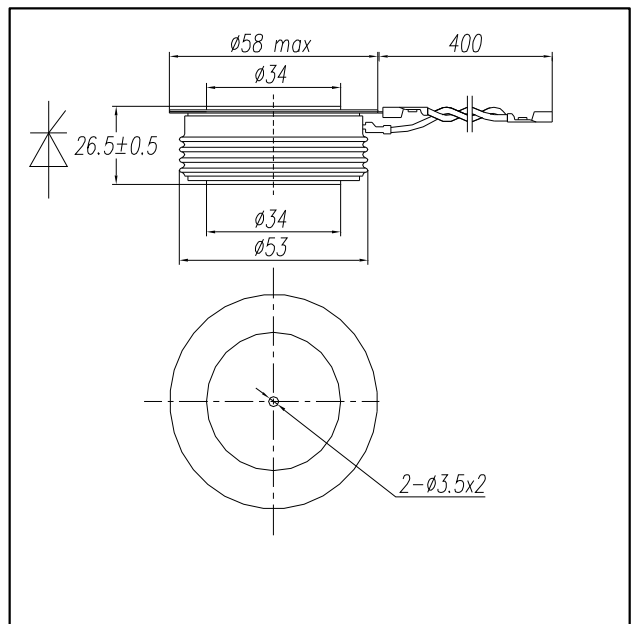
Thermal & Mechanical Data

Symb.	Parameter	Min	Type	Max	Unit
R_{thjc}	Thermal Resistance Junction to Case	-	-	0.035	K/W
R_{thcs}	Thermal Resistance Case to Heatsink	-	-	0.008	K/W
T_{vj}	Junction Temperature	-40	-	125	°C
T_{stg}	Storage Temperature	-40	-	140	°C
F	Mounting Force	-	15	-	kN
m	Weight	-	0.26	-	kg

Voltage Ratings

Device Type	$V_{DRM}/V_{RRM}(V)$	Test Conditions
T808 750-20	2000	$T_{vj} = 125\text{ °C}$
T808 750-22	2200	$I_{DRM} = 60\text{ mA}$
T808 750-24	2400	$I_{RRM} = 60\text{ mA}$
T808 750-26	2600	$V_{DM} = V_{DRM}, V_{RM} = V_{RRM}$ $t_p = 10\text{ ms}$ $V_{DSM} = V_{DRM}$ $V_{RSM} = V_{RRM} + 100$

Outline



Current Ratings

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
$I_{T(AV)}$	Mean On-State Current	Half Sine Wave, $T_C = 70\text{ °C}$	-	-	750	A
$I_{T(RMS)}$	RMS On-State Current	$T_C = 70\text{ °C}$	-	-	1178	A
I_{TSM}	Surge (non-repetitive) On-State Current	10ms, Half Sine Wave, $T_C = 125\text{ °C}, V_R = 0$	-	-	11.0	kA
I^2t	Limiting load integral	Sine Wave, 10ms	-	-	60.5	$10^4 A^2s$

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Characteristics

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
V_{TM}	Peak on-state voltage	$T_{vj} = 125^{\circ}C, I_{TM} = 1500 A$	-	-	1.7	V
I_{DRM}	Forward leakage current	$T_{vj} = 125^{\circ}C, V_{DRM}$	-	-	60	mA
I_{RRM}	Reverse leakage current	$T_{vj} = 125^{\circ}C, V_{RRM}$	-	-	60	mA
V_{TO}	Threshold voltage	$T_{vj} = 125^{\circ}C$	-	-	0.95	V
r_T	Slope resistance	$T_{vj} = 125^{\circ}C$	-	-	0.5	m Ω
I_H	Holding current	$T_{vj} = 25^{\circ}C$	-	-	200	mA
I_L	Latching current	$T_{vj} = 25^{\circ}C$	-	-	1000	mA

Dynamic Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
dv/dt	Critical rate of rise of off-state voltage	$T_{vj} = 125^{\circ}C, 0.67V_{DRM}$	1000	-	-	V/ μs
di/dt	Critical rate of rise of on-state current	$T_{vj} = 125^{\circ}C, V_{DM} = 0.67V_{DRM}, I_{TM} = 1000A$ $I_{FG} = 2 A, t_r = 0.5 \mu s, f = 50 Hz$	-	-	200	A/ μs
t_d	Delay time	$T_{vj} = 25^{\circ}C, V_{DM} = 0.5V_{DRM}, I_{TM} = 1000 A$ $I_{FG} = 2 A, t_r = 0.5 \mu s$	-	-	3.0	μs
t_q	Turn-off time	$T_{vj} = 125^{\circ}C, V_{DM} = 0.67V_{DRM}, dv/dt = 20V/\mu s, V_R = 200V$ $di_T/dt = -10 A/\mu s, I_T = 1000 A$	-	250	-	μs
Q_{rr}	Recovery Charge	$T_{vj} = 125^{\circ}C, di_T/dt = -10A/\mu s, V_R = 200V,$ $I_T = 1000A$	-	-	2200	μC
I_{rr}	Reverse recovery current		-	-	125	A

Gate Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
I_{GT}	Gate trigger current	$T_{vj} = 25^{\circ}C$	-	-	300	mA
V_{GT}	Gate trigger voltage	$T_{vj} = 25^{\circ}C$	-	-	3.0	V
I_{GD}	Gate non-trigger current	$T_{vj} = 125^{\circ}C, V_D = 0.4V_{DRM}$	10	-	-	mA
V_{GD}	Gate non-trigger voltage	$T_{vj} = 125^{\circ}C, V_D = 0.4V_{DRM}$	0.3	-	-	V
V_{FGM}	Peak forward gate voltage		-	-	12	V
V_{RGM}	Peak reverse gate voltage		-	-	5	V
I_{FGM}	Peak forward gate current		-	-	4	A
P_{GM}	Gate power losses		-	-	20	W
$P_{G(AV)}$	Gate power losses (mean)		-	-	4	W

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Max. on-state characteristic model

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

	25 °C	125 °C
A	0.740638	0.898652
B	0.044871	-0.003469
C	0.000371	0.000504
D	0.002746	0.001585

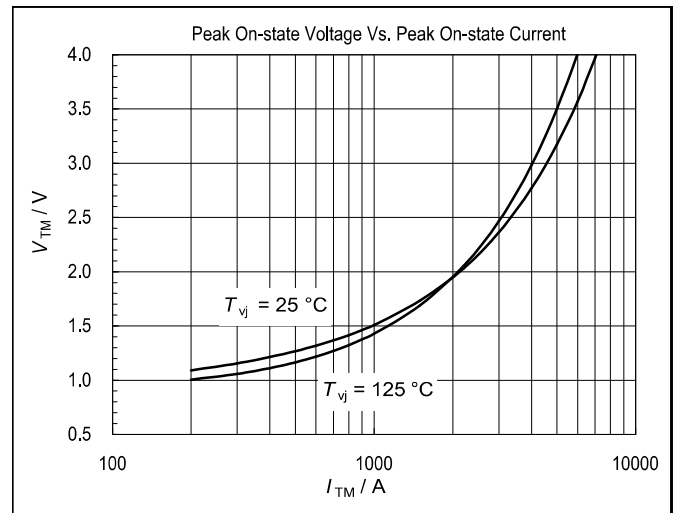


Fig1. Peak On-state Voltage Vs. Peak On-state Current

Transient thermal impedance function
(double side cooled)

$$R_{thjc}(t) = \sum_{i=1}^n R_{thi} \cdot \left(1 - e^{-\frac{t}{\tau_i}}\right)$$

i	1	2	3	4
R _{thi} (K/kW)	19.719	4.2406	7.9638	3.0437
τ _i (s)	0.7086	0.1436	0.0362	0.0021

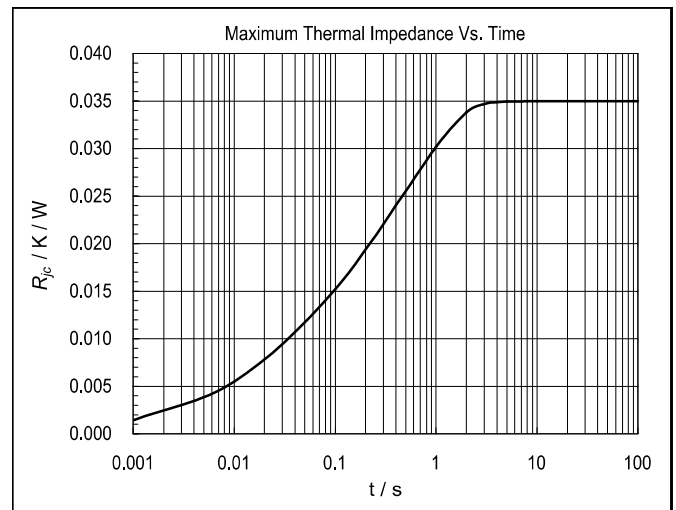


Fig2. Maximum Thermal Impedance Vs. Time

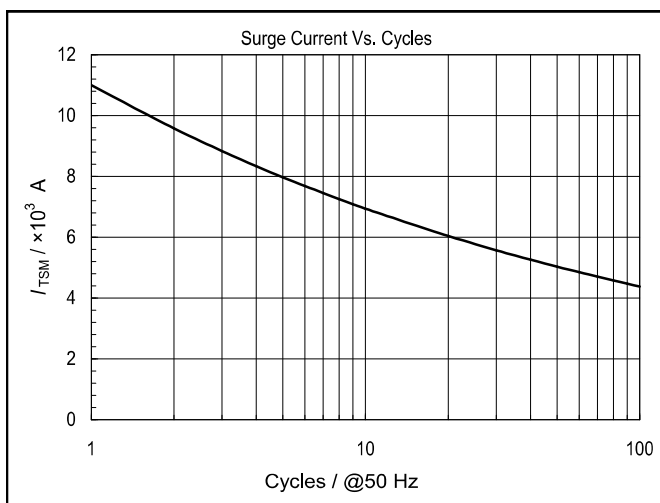


Fig3. Surge Current Vs. Cycles

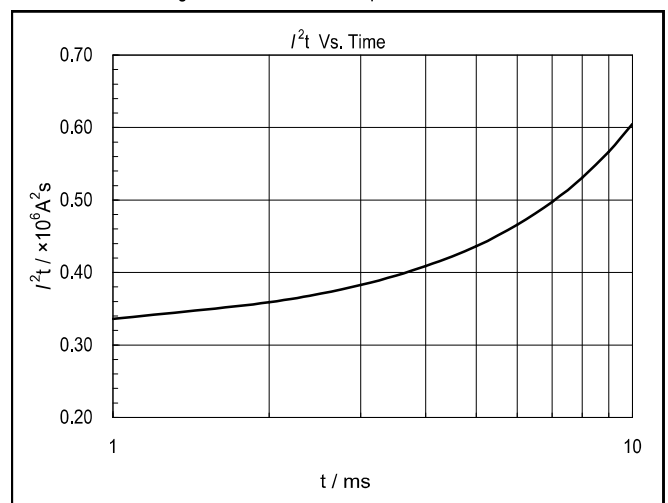


Fig4. I²t Vs. Time

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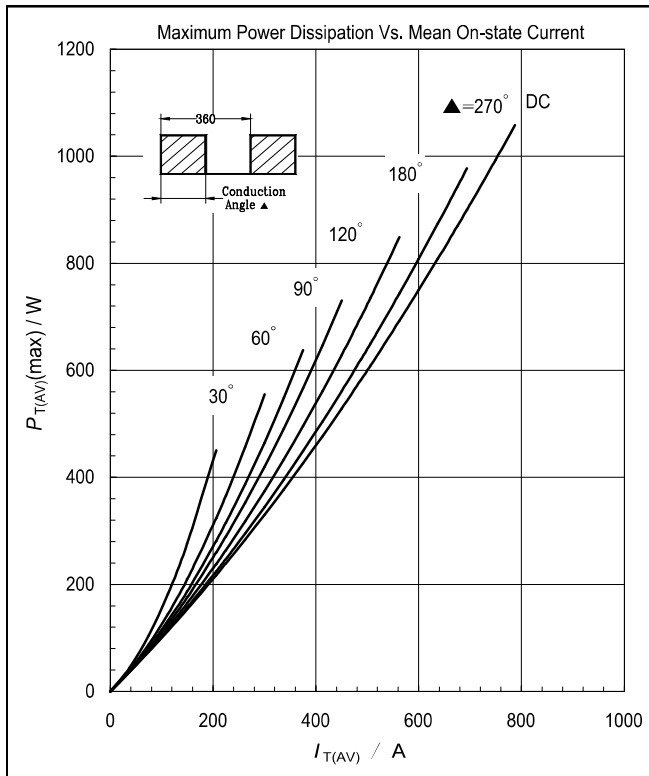


Fig5. Maximum Power Dissipation Vs. Mean On-state Current

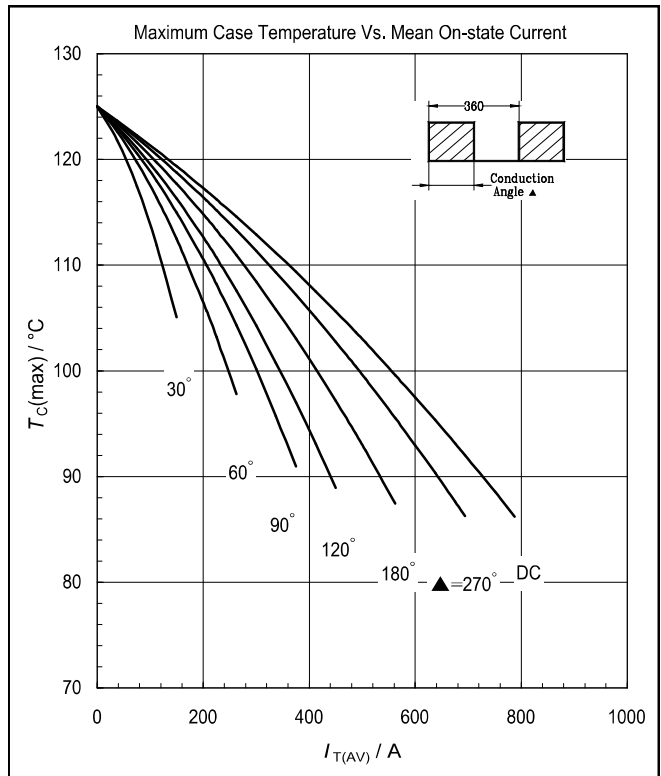


Fig6. Maximum Case Temperature Vs. Mean On-state Current

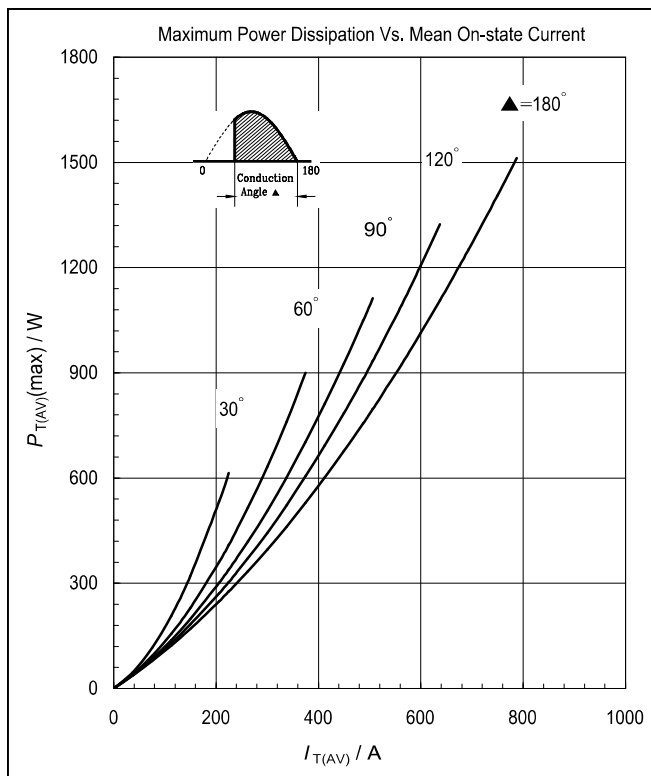


Fig7. Maximum Power Dissipation Vs. Mean On-state Current

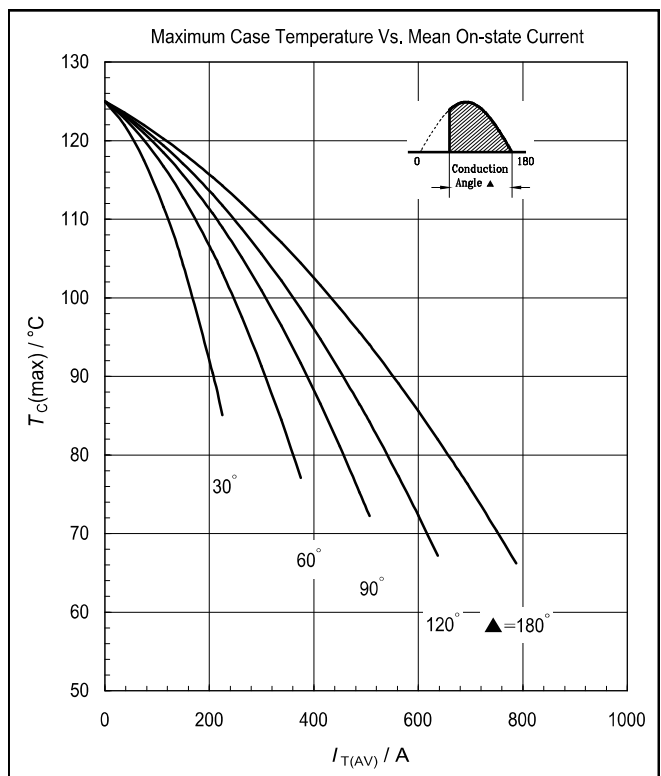


Fig8. Maximum Case Temperature Vs. Mean On-state Current

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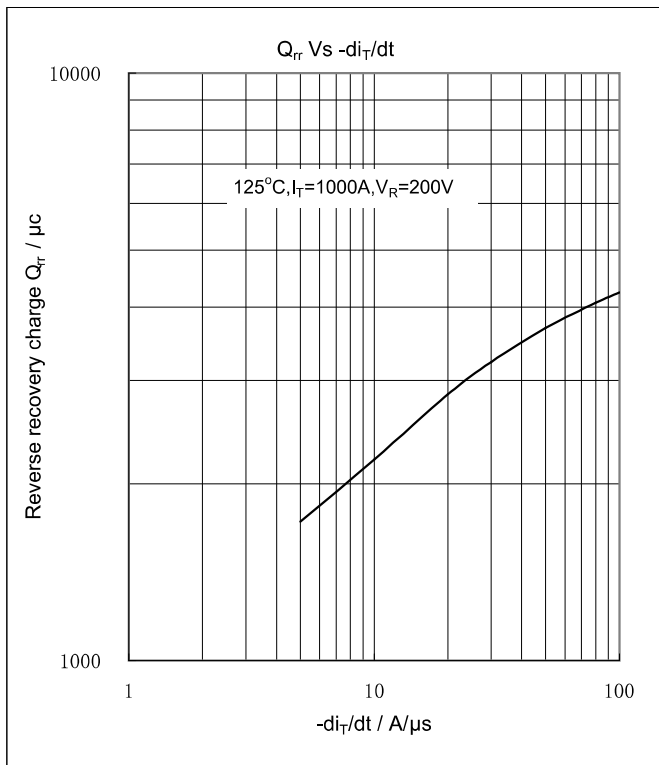


Fig9. Reverse recovery charge Vs. $-di_T/dt$

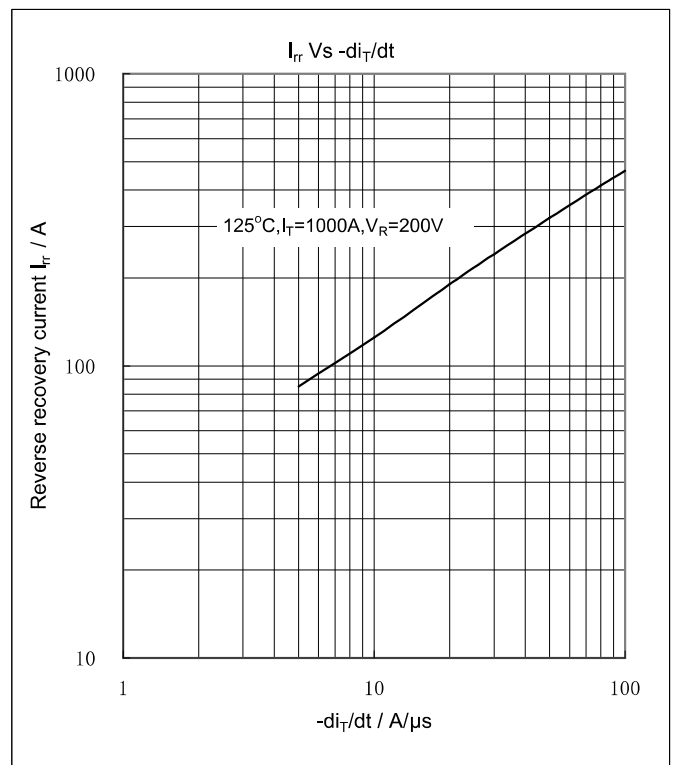


Fig10. Reverse recovery current Vs. $-di_T/dt$

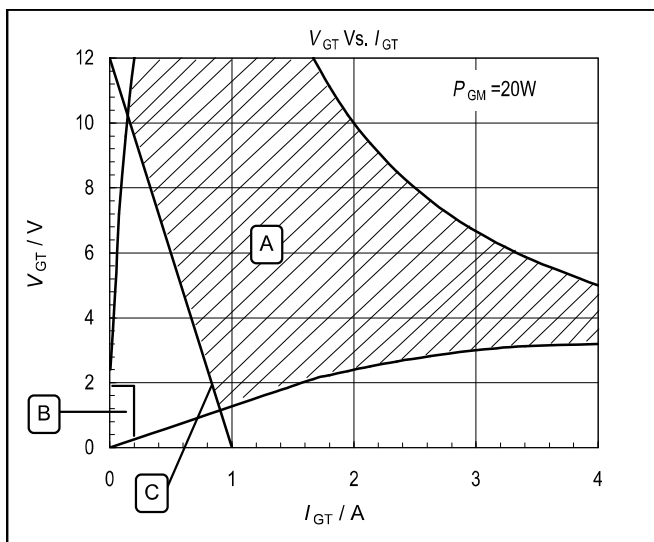


Fig11. V_{GT} Vs. I_{GT}

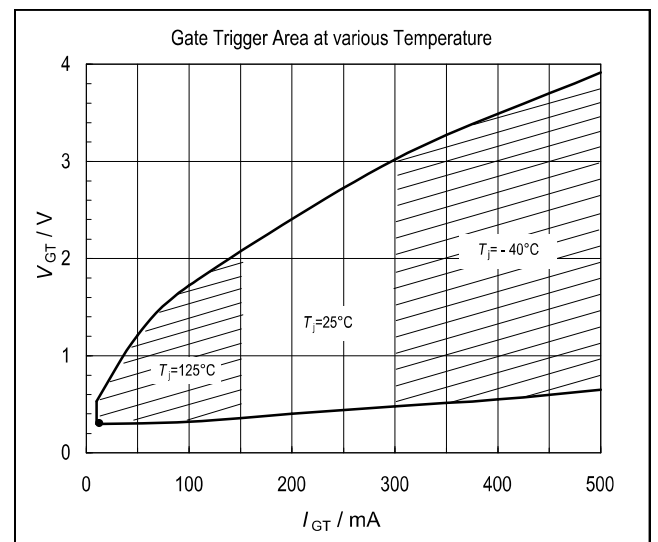


Fig12. Gate Trigger Area at various Temperature

A is Recommended Triggering Area.

B is Unreliable Triggering Area.

C is Recommended Gate Load Line.